

# NTST20120CTG, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG, NTSB20120CTT4G

## Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.54\text{ V}$  at  $I_F = 5\text{ A}$

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

### Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

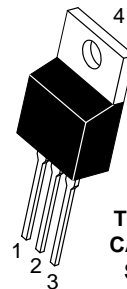
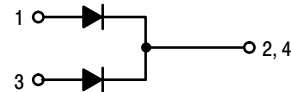


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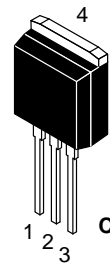
[www.onsemi.com](http://www.onsemi.com)

VERY LOW FORWARD  
VOLTAGE, LOW LEAKAGE  
SCHOTTKY BARRIER  
RECTIFIERS 20 AMPERES,  
120 VOLTS

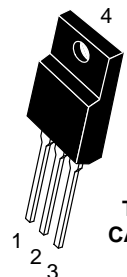
### PIN CONNECTIONS



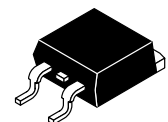
TO-220AB  
CASE 221A  
STYLE 6



I2PAK  
CASE 418D  
STYLE 3



TO-220FP  
CASE 221AH



D2PAK  
CASE 418B

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# NTST20120CTG, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG, NTSB20120CTT4G

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	120	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 130^\circ\text{C}$ )	$I_{F(AV)}$ Per device Per diode	20 10	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 135^\circ\text{C}$ )	$I_{FRM}$ Per device Per diode	40 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	120	A
Operating Junction Temperature	$T_J$	-40 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	NTST20120CTG NTSB20120CT-1G	NTSB20120CTG	NTSJ20120CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.5 70	1.43 46.8	4.42 105	$^\circ\text{C/W}$ $^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.62 0.90  0.54 0.64	– 1.10  – 0.72	V
Maximum Instantaneous Reverse Current (Note 1) ( $V_R = 90\text{ V}$ , $T_J = 25^\circ\text{C}$ ) ( $V_R = 90\text{ V}$ , $T_J = 125^\circ\text{C}$ )  (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	12 6  – 17	– –  700 100	$\mu\text{A}$ mA  $\mu\text{A}$ mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

NTST20120CTG, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG,  
NTSB20120CTT4G

TYPICAL CHARACTERISTICS

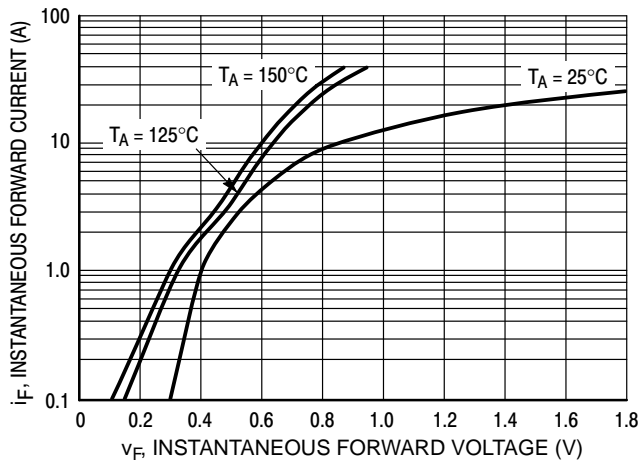


Figure 1. Typical Instantaneous Forward Characteristics

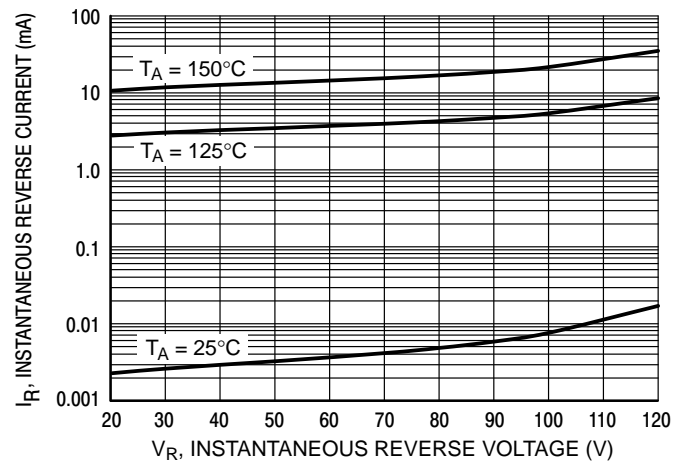


Figure 2. Typical Reverse Current Characteristics

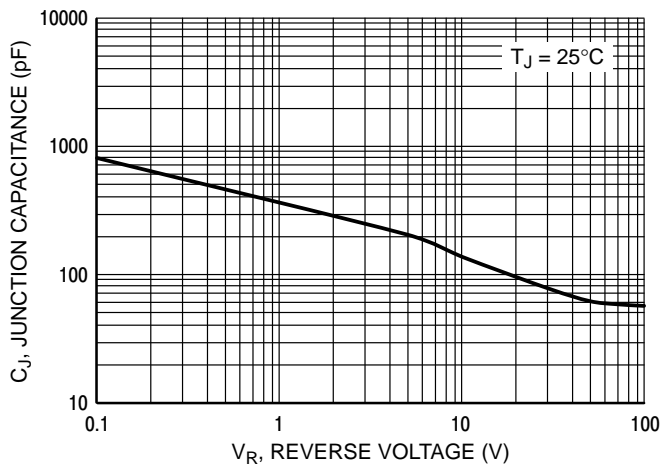


Figure 3. Typical Junction Capacitance

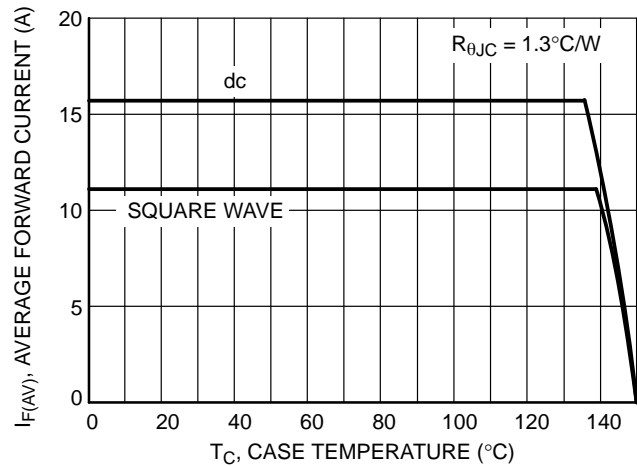


Figure 4. Current Derating per Leg

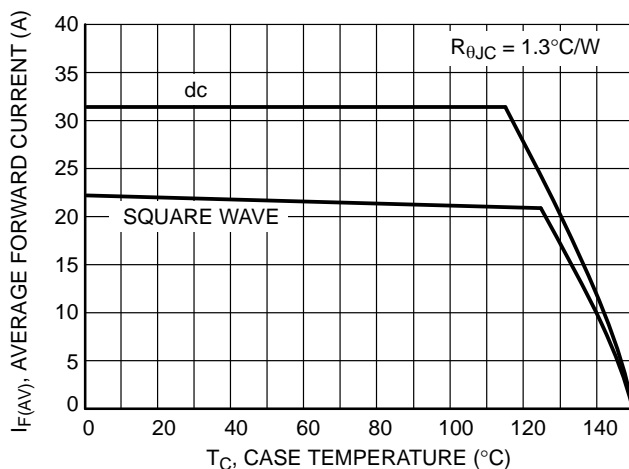


Figure 5. Current Derating

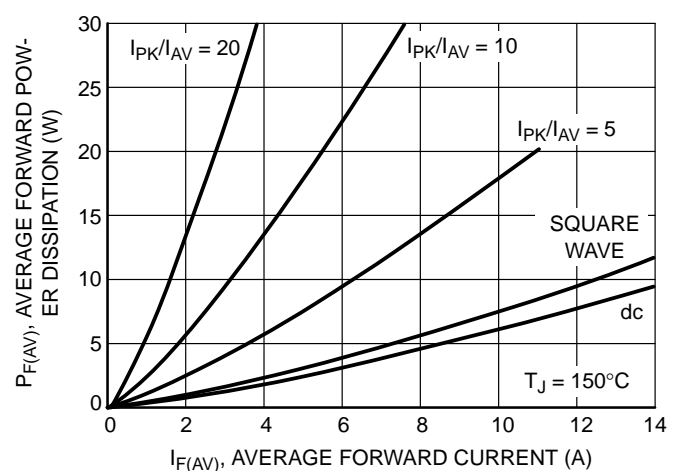
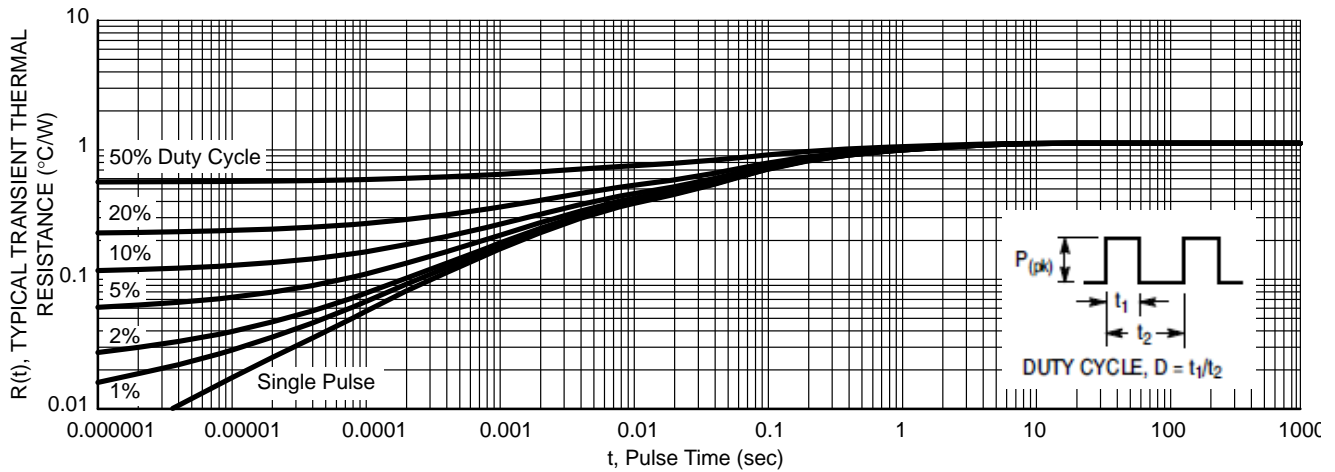


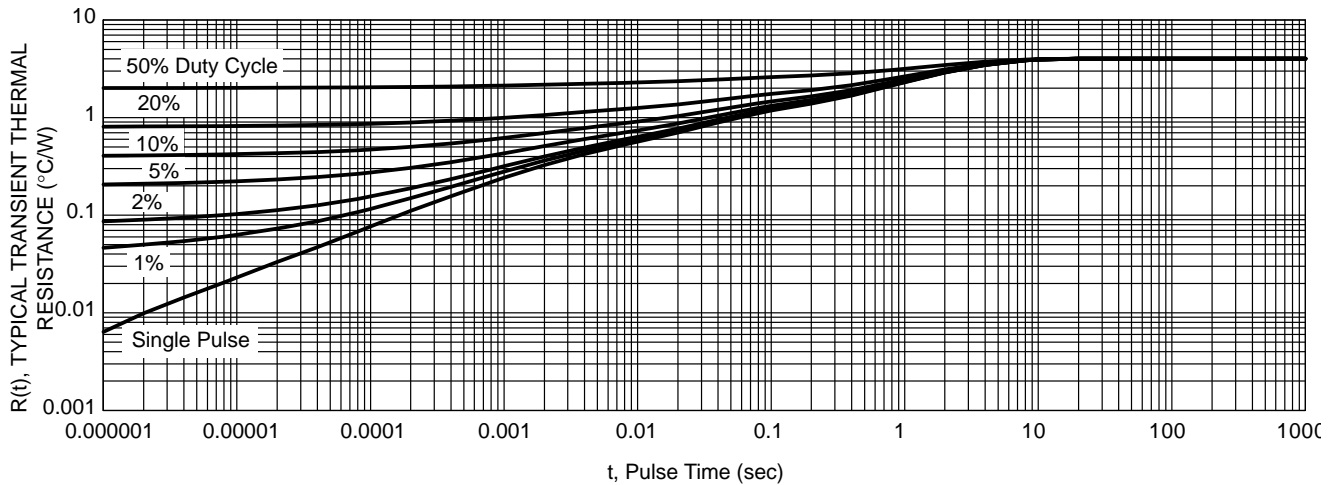
Figure 6. Forward Power Dissipation

**NTST20120CTG, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG,  
NTSB20120CTT4G**

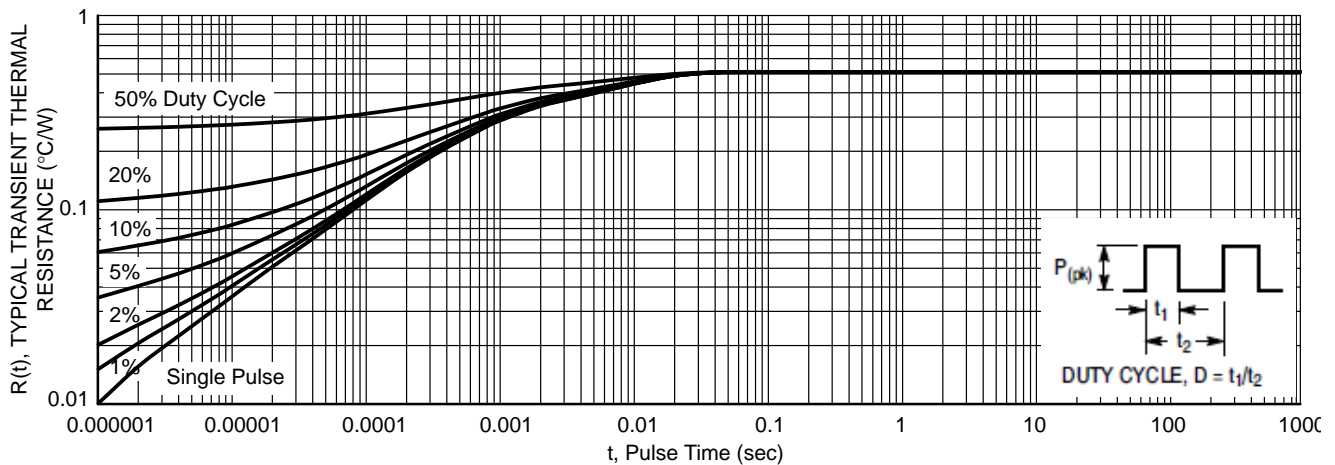
**TYPICAL CHARACTERISTICS**



**Figure 7. Typical Transient Thermal Response for NTST20120CT and NTSB20120CT-1G**



**Figure 8. Typical Transient Thermal Response for NTSJ20120CTG**



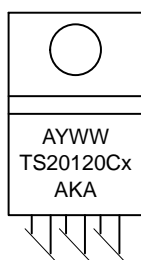
**Figure 9. Typical Transient Thermal Response for NTSB20120CTG**

# NTST20120CTG, NTSJ20120CTG, NTSB20120CT-1G, NTSB20120CTG, NTSB20120CTT4G

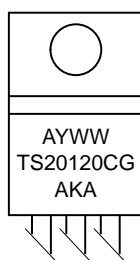
## ORDERING INFORMATION

Device	Package	Shipping
NTST20120CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSJ20120CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB20120CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB20120CTG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB20120CTT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

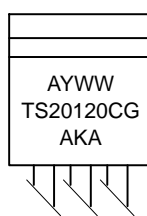
## MARKING DIAGRAMS



TO-220AB



TO-220FP



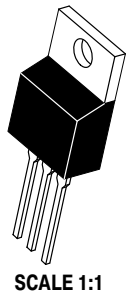
I<sup>2</sup>PAK



D<sup>2</sup>PAK

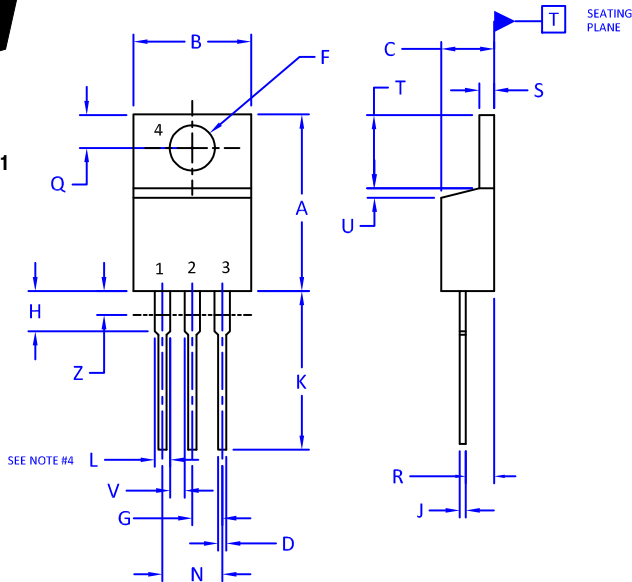
A = Assembly Location  
 Y = Year  
 WW = Work Week  
 AKA = Polarity Designator  
 x = G or H  
 G = Pb-Free Package  
 H = Halide-Free Package

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



## TO-220 CASE 221A ISSUE AK

DATE 13 JAN 2022



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	----	1.15	---
Z	----	0.080	---	2.04

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR  
4. EMITTER

STYLE 3:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 4:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

STYLE 5:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 8:  
PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

STYLE 9:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 10:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

STYLE 11:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

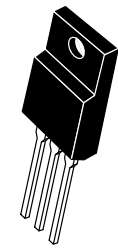
STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED

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DESCRIPTION:	TO-220	PAGE 1 OF 1

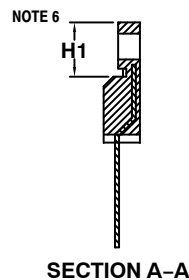
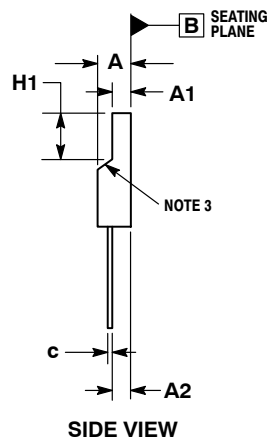
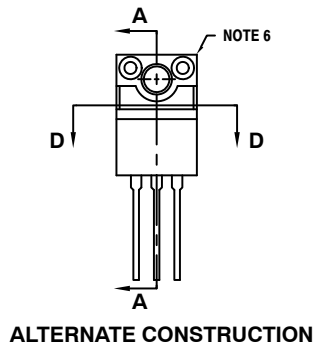
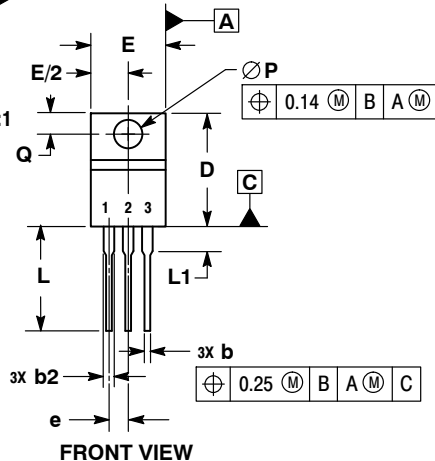
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### TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F

DATE 30 SEP 2014



SCALE 1:1

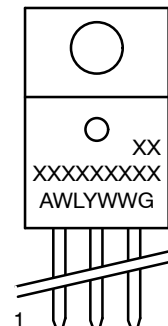


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

#### GENERIC MARKING DIAGRAM\*



A = Assembly Location  
WL = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE

STYLE 2:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

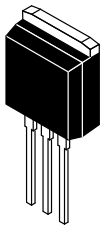
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DESCRIPTION:	TO-220 FULLPACK, 3-LEAD	PAGE 1 OF 1

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

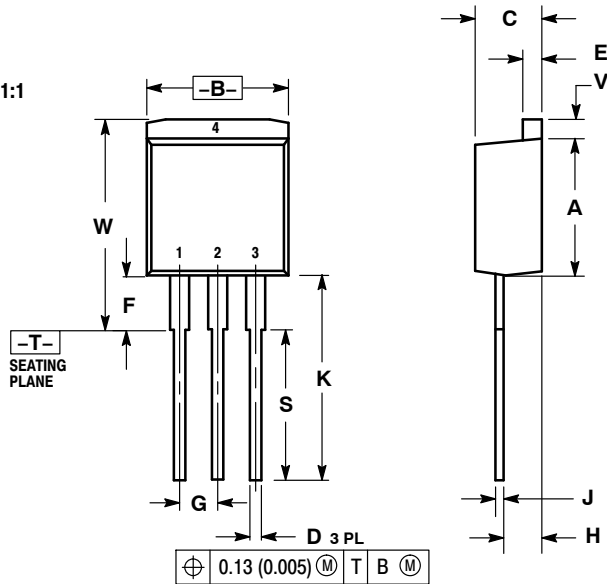
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SCALE 1:1

### I<sup>2</sup>PAK (TO-262) CASE 418D-01 ISSUE D

DATE 16 OCT 2007



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

#### STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

#### STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

#### STYLE 3:

- PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

#### STYLE 4:

- PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

DOCUMENT NUMBER: 98ASB16716C

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DESCRIPTION: I<sup>2</sup>PAK (TO-262)

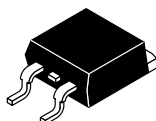
PAGE 1 OF 1

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

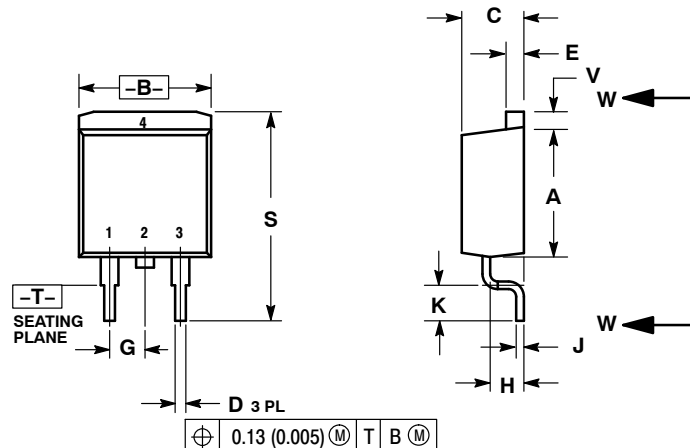
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

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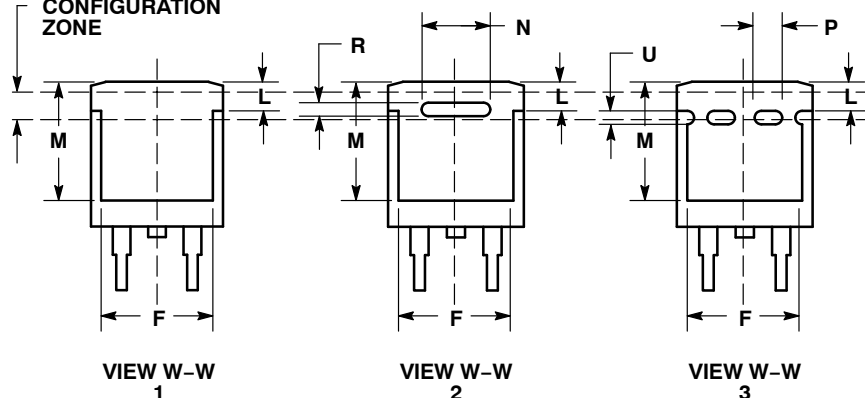


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

**VARIABLE  
CONFIGURATION  
ZONE**



**STYLE 1:**

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

**STYLE 2:**

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

**STYLE 3:**

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

**STYLE 4:**

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

**STYLE 5:**

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

**STYLE 6:**

- PIN 1. NO CONNECT
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

## MARKING INFORMATION AND FOOTPRINT ON PAGE 2

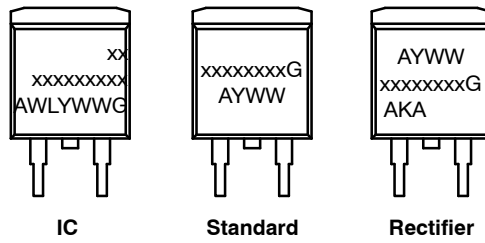
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

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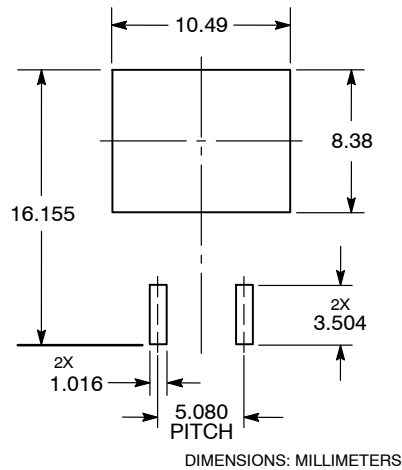
**GENERIC  
MARKING DIAGRAM\***



xx        = Specific Device Code  
A        = Assembly Location  
WL      = Wafer Lot  
Y        = Year  
WW      = Work Week  
G        = Pb-Free Package  
AKA     = Polarity Indicator


\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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